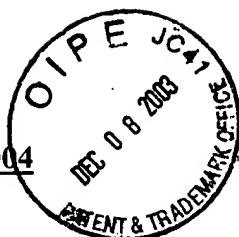


S/N 09/691004

PATENT



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant:	Leonard Forbes et al.	Examiner:	Johannes P Mondt
Serial No.:	09/691004	Group Art Unit:	2826
Filed:	October 18, 2000	Docket:	303.324US4
Title:	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE		

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(c)(2), Applicants have included the fee of \$180.00 as set forth in 37 C.F.R. §1.17(p). Please charge any additional fees or credit any overpayment to Deposit Account No. 19-0743.

RECEIVED  
DEC 16 2003  
TECHNOLOGY CENTER 2800

09/691004 00000020 09691004

12 001806

180.00 DP

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Serial No :09/691004

Filing Date: October 18, 2000

Title: TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE

Page 2

Dkt: 303.324US4

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

LEONARD FORBES ET AL.

By their Representatives,


SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

P.O. Box 2938

Minneapolis, MN 55402

(612) 373-6973

Date 2 December 2003

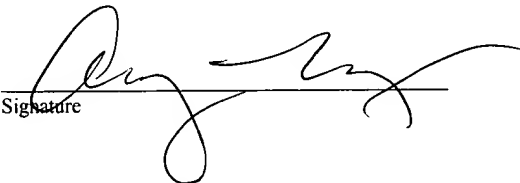
By   
Robert E. Mates  
Reg. No. 35,271

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 2nd day of December, 2003.

Name

Amy Moriarty

Signature



S/N 09/691004

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al. Examiner: Johannes P. Mondt  
Serial No.: 09/691004 Group Art Unit: 2826  
Filed: October 18, 2000 Docket: 303.324US4  
Title: TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND  
METHODS OF FABRICATION AND USE

COMMUNICATION CONCERNING RELATED APPLICATION(S)

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
09/256643	February 23, 1999	303.324US2	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
09/652420	August 31, 2000	303.324US3	TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE
08/903486	July 29, 1997	303.326US1	SILICON CARBIDE GATE TRANSISTOR
09/259870	March 1, 1999	303.326US2	FABRICATION OF SILICON CARBIDE GATE TRANSISTOR
08/902132 5886368	July 29, 1997	303.353US1	TRANSISTOR WITH SILICON OXYCARBIDE GATE AND METHODS OF FABRICATION AND USE
09/138294 6309907	August 21, 1998	303.353US2	TRANSISTOR WITH SILICON OXYCARBIDE GATE AND METHODS OF FABRICATION AND USE

RECEIVED  
DEC 16 2003  
TECHNOLOGY CENTER 800

COMMUNICATION CONCERNING RELATED APPLICATIONS

Serial Number: 09/691004

Filing Date: October 18, 2000

Title: TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE

---

Page 2

Dkt: 303.324US4

08/902843	July 29, 1997	303.354US1	DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE INSULATOR
09/135413	August 14, 1998	303.354US2	METHOD FOR OPERATING A DEAPROM HAVING AN AMORPHOUS SILICON CARBIDE GATE INSULATOR
09/134713	August 14, 1998	303.354US3	DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE INSULATOR
08/902098 6031263	July 29, 1997	303.355US1	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
09/140978 6307775	August 27, 1998	303.355US2	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
09/141392 6249020	August 27, 1998	303.355US3	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
09/883795	June 18, 2001	303.355US4	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
10/047181	October 23, 2001	303.355US5	DEAPROM AND TRANSISTOR WITH GALLIUM NITRIDE OR GALLIUM ALUMINUM NITRIDE GATE
08/902133	July 29, 1997	303.356US1	MEMORY DEVICE
10/231687	August 29, 2002	303.356US2	DYNAMIC ELECTRICALLY ALTERABLE PROGRAMMABLE READ ONLY MEMORY DEVICE
08/903453	July 29, 1997	303.378US1	CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS
09/258467	February	303.378US2	CARBURIZED SILICON GATE

COMMUNICATION CONCERNING RELATED APPLICATIONS

Serial Number: 09/691004

Filing Date: October 18, 2000

Title: TRANSISTOR WITH VARIABLE ELECTRON AFFINITY GATE AND METHODS OF FABRICATION AND USE

Page 3

Dkt: 303.324US4

26, 1999

INSULATORS FOR INTEGRATED  
CIRCUITS

09/650553

August 30,  
2000

303.378US3

CARBURIZED SILICON GATE  
INSULATORS FOR INTEGRATED  
CIRCUITS

10/461593

June 11,  
2003

303.356US3

DYNAMIC ELECTRICALLY  
ALTERABLE PROGRAMMABLE  
READ ONLY MEMORY DEVICE

Respectfully submitted,


LEONARD FORBES ET AL.

By Applicants' Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.  
P.O. Box 2938  
Minneapolis, MN 55402  
(612) 373-6973

Date 2 December 2003

By

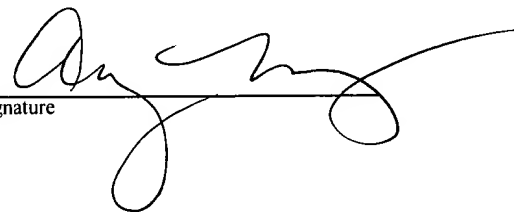
  
Robert E. Mates  
Reg. No. 35,271

CERTIFICATE UNDER 37.CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 2nd day of December, 2003.

Name

Amy Moriarty

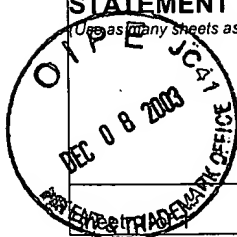
Signature



Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)



Complete if Known

Application Number	09/691004
Filing Date	October 18, 2000
First Named Inventor	Forbes, Leonard
Group Art Unit	2826
Examiner Name	Mondt, Johannes

Attorney Docket No: 303.324US4

**US PATENT DOCUMENTS**

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
	US-4,736,317	04/05/1988	Hu, M. , et al.	364	200	07/17/1985
	US-4,980,303	12/25/1990	Yamauchi, T.	437	31	08/18/1988
	US-5,189,504	02/23/1993	Nakayama, S. , et al.	257	422	01/30/1992
	US-5,336,361	08/09/1994	Tamura, A. , et al.	438	767	11/02/1992
	US-5,360,491	11/01/1994	Carey, P G., et al.	136	256	04/07/1993
	US-5,367,306	11/22/1994	Hollon, , et al.	342	386	06/04/1993
	US-5,409,501	04/25/1995	Zauns-Huber, R. , et al.	8	94.29	07/06/1992
	US-5,425,860	06/20/1995	Truher, J. B., et al.	204	192.23	04/07/1993
	US-5,623,160	04/22/1997	Liberkowsky, J. B.	257	621	09/14/1995
	US-5,990,531	11/23/1999	Taskar, N. R., et al.	257	410	11/12/1997
	US-6,100,193	08/08/2000	Suehiro, S. , et al.	438	685	09/24/1997
	US-6,166,768	12/26/2000	Fossum, , et al.	348	308	01/22/1997
	US-6,365,919	04/02/2002	Tihanyi, J. , et al.	257	77	07/11/2000

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
	JP-60-024678	02/07/1985	Akio, Nakatani	G06 K	9/36	

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
--------------------	----------------------	---	----------------

RECEIVED  
DEC 16 2003  
TECHNOLOGY CENTER 2800

EXAMINER

DATE CONSIDERED